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INFORMATION DISCLOSURE  
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(Use several sheets if necessary)

Sheet 1 of 3

ATTY. DOCKET NO. UMC-96-279  
CON  
Client/Matter No. 81848.0016.001

APPLICATION NO.: 09/546,174

FIRST NAMED INVENTOR:

CHIH-CHIEN LIU

FILING DATE  
APRIL 11, 2000

ART UNIT 1711

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U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document No. No. - Kind Code	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Doc	Class	Subclass
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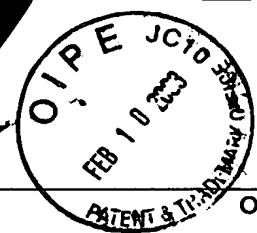
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						YES	NO

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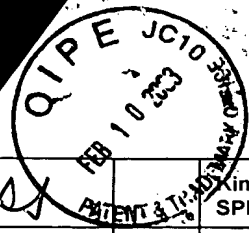
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EXAMINER SIGNATURE <i>Ruben Bryant</i>	
DATE CONSIDERED 6/1/03	
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